

INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)		Docket No.: YOR920030207US1	Serial No.:			
		Applicant(s): Hyungjun KIM et al.				
		Filing Date:	Group:			
U.S. PATENTS						
Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date
<i>QCS</i>	2003/0201537A	10/30/03	Lane et al. KIM et al.			
<i>QCS</i>	U.S. Patent Application Serial No. 10/699,226					
FOREIGN PATENT DOCUMENTS						
Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a	
OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)						
<i>QCS</i>	Rossnagel et al., Plasma-enhanced atomic layer deposition of Ta and Ti for inter-connect diffusion barriers, J. Vac. Sci. Technol. B 18(4), July/Aug 2002					
<i>QCS</i>	KIM et. al., Growth of cubic-TaN thin films. J.App.Physics, Vol. 92, No.12,2002					
<i>QCS</i>	Kim et al., Growth kinetics and initial stage growth during plasma-enhanced Ti atomic layer deposition, J. Vac. Sci. Technol. A 20(3), May/June 2002					
<i>QCS</i>	Kim et al., Diffusion barrier properties of transition metal thin films grown by plasma-enhanced atomic layer deposition, J.Vac.Sci.Technol. B 20(4), J/A 2002					
Examiner's Signature: <i>Radio C. Swanson</i>			Date Considered: <i>05/12/05</i>			
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).						